ABSTRACT OF THE DISCLOSURE

A display device in which variations of characteristics of a TFT are eliminated and the aperture ratio is improved is provided. A display device has a thin film transistor on an insulating substrate 10. The thin film transistor includes first gate electrodes 11, a gate insulating film 12, a semiconductor film 13 which is formed on the first gate electrode 11, and a interlayer insulating film 15. The thin film transistor further includes second gate electrodes 70 which are on the interlayer insulating film 15 and at least above channels 13c, and which are connected to the first gate electrodes 11. A reflective display electrode 19 connected to the source of the thin film transistor is elongated to extend above the thin film transistor.